Hall Ticket Number :						
						R-14

Code: 4G513

B.Tech. I Year Supplementary Examinations May 2017

Engineering Drawing

(Common to EEE, ECE, CSE and IT)

Max. Marks: 70

Time: 3 Hours

Answer all five units by choosing one question from each unit (5 x 14 = 70 Marks)

UNIT–I

1. Construct a hyperbola, with the distance between the focus and the directrix as 50mm and eccentricity as 3/2. Also, draw normal and tangent to the curve at a point 30 mm from the axis.

OR

2. Draw an epicycloid of rolling circle 40mm diameter, which rolls outside another circle of 150 mm diameter for one revolution.

UNIT-II

3. Draw the projections of the following points on a common reference line.

- i) P 35mm behind the VP and 20mm below the HP
- ii) Q 40mm in front the VP and 30mm above the HP
- iii) R 50mm behind the VP and 15mm above the HP
- iv) S 40mm below the HP and in the VP
- v) T 30 mm in front of the VP and 50mm below the HP

OR

4. A line PQ 70 mm long has its end P 10 mm above H.P and 15 mm in front of V.P. Its top view and front view measure 60 mm and 40 mm respectively. Draw the projections of the line and determine its inclinations with H.P and V.P

UNIT–III

5. A hexagonal plate of side 20 mm rests on the HP on one of its sides inclined at 45° to the VP. The surface of the plate makes an angle of 300 with the H.P. Draw the front and top views of the plate.

OR

6. A regular pentagonal lamina ABCDE of side 30 mm has one of its edges parallel to the VP and inclined at 30° to the HP. The pentagon is inclined at 45° to the VP. Draw the projections.

UNIT–IV

7. A Square pyramid of base side 30 mm and axis length 50 mm has one of its triangular faces in the VP and the axis parallel to and 25 mm above the HP. Draw its top and front views.

OR

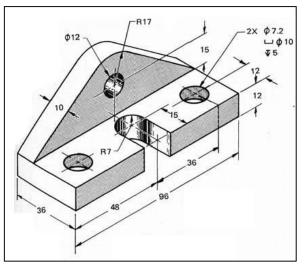
8. Draw the projections of a hexagonal prism of base 25 mm side and axis 60 mm long resting on one of its corners of the base on HP. The axis of the solid is inclined at 450 to HP.

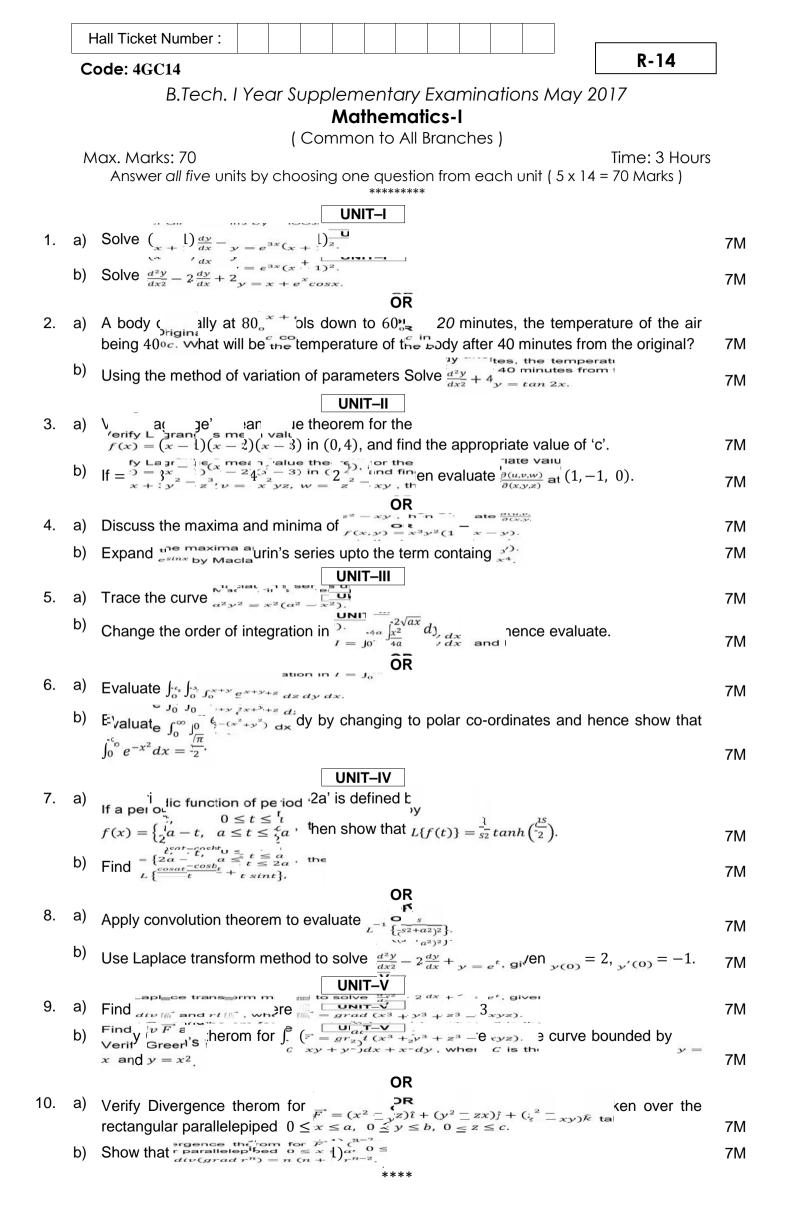
UNIT-V

9. A pentagonal prism, 30 mm edge of base and 65 mm height, stand on HP such that an edge of the base is parallel to VP and nearer to it. Draw the isometric view of the prism.

OR

10. Sketch the front view and top view of the object given in figure below.





Hall T	icke	et Number :	
Code	: 4 0	R-14	
		B.Tech. I Year Supplementary Examinations May 2017	
		Programming in C and Introduction to Datastructures	
Max.	Мс	(Common to CE, EEE, ME and ECE) arks: 70 Time: 3 Hou	Jrs
		Il five units by choosing one question from each unit (5 x 14 = 70 Marks	
		********* UNIT–I	
1	a)	Define	
		i) Algorithm.	
		ii) Flowchart	4M
	b)	Explain the structure of a C program with example	4M
	c)	Write a C program to find average of six subject marks.	6M
		OR	
2	a)	Explain in details about computing environments	7M
	b)	Write a C program to swap two integer numbers.	7M
3	\sim	UNIT-II Explain in detail about switch statement.	7M
5	a) b)	Write a C program to generate multiplication table.	7M
	5)	OR	7 1 1 1
4	a)	How do you declare a one dimensional array? Write a C program to find sum	
•	с,	the sum of elements initialized in one dimensional array.	7M
	b)	Describe the purpose of break and continue statements in C	7M
		UNIT–III	
5	a)	Define Pointer. List the features of Pointers	7M
	b)	Explain in detail about call by value and call by reference.	7M
		OR	
6	a)	List the names of the functions supported in the header file "stdio.h" and specify the purpose of at least three functions.	8M
	b)	Explain about malloc() and calloc()	6M
	5)		OIVI
7	a)	Write a program in C to search for an element using binary search technique	7M
	b)	Define Structures. Explain with an example how structure members are	
		initialized and accessed	7M
		OR	
8	a)	Explain merge sort with an examples	8M
	b)	Differentiate between structures and unions.	6M
0	2)	UNIT-V	714
9	a) b)	Write a program in C to evaluate postfix expression. Define Stack. Explain the push and pop operation of Stack	7M 7M
	D)	OR	7 111
10	a)	When we will use circular queues instead of queues. Explain the insert and	
.0	4)	delete operation of circular queue	9M
	b)	What are the applications of queues?	5M

Hall Ticket Number : R-14	
Code: 4G311	
B.Tech. I Year Supplementary Examinations May 2017	
Electronic Devices & Circuits	
(Common to EEE & ECE) Max. Marks: 70 Time: 3 Hours	
Answer all five units by choosing one question from each unit (5 x 14 = 70 Marks)	
UNIT–I 1. a) State and explain Kirchhoff voltage and current law with an example	8
b) Explain about Maximum Power transfer theorem	6
OR	0
2. a) State the Norton's theorem	4
b) From the circuit shown below determine the current through the 10 resistor using	
Thévenin's theorem	,
A	
$E_2 6V$	
$R_3 \prod 10\Omega$	
$E_1 \longrightarrow 9V$ $R_2 \square 1.5\Omega$	
	10
UNIT-II 3. a) What do you understand by depletion region at PN junction? What is the effect o	f
3. a) What do you understand by depletion region at PN junction? What is the effect o forward and reverse biasing of PN junction on the depletion region? Explain with	
necessary diagrams.	8
b) Derive the expression for rectification efficiency of Full wave rectifier circuit	6
OR	
4. a) Sketch the energy band diagram of an open-circuited PN-junction. Explain the terms	
'depletion region', 'potential barrier', and 'barrier energy'.	8
b) Explain how Zener diode acts as a voltage regulator UNIT-III	6
5. a) Explain the input and output characteristics of the transistor in CE configuration with	า
diagrams.	. 6
b) Draw the Transistor biasing circuit using fixed bias arrangement and explain its	\$
principle with suitable analysis.	8
	_
 6. a) Explain the operation of NPN transistor with neat diagrams b) Draw the Transister biasing sizewit using Valtage divider bias errongement and explain 	6
 b) Draw the Transistor biasing circuit using Voltage divider bias arrangement and explain its principle with suitable analysis. 	ו 8
7. a) Draw fixed biasing circuit of N-Channel FET and explains the function of each	ı
component in the circuit in fixing the quiescent operating conditions of amplifiers	8
b) Explain the principle of MOSFET in depletion mode.	6
OR	
 What are the biasing schemes available to achieve the required bias in a junction field effect transistor? Explain any one of the biasing schemes. 	d 8
Explain the operation of enhancement mode MOSFET	6
	U
9. a) Sketch the four-layer construction of an SCR and the two-transistor equivalent circuit	
Explain the device operation	7
b) Explain the principle and working of phototransistor with diagrams	7
OR	
10. a) Draw the circuit diagram to obtain the UJT characteristics between the Emitter voltage	
'VE' and the Emitter current 'IE' for a fixed value of 'VBB'.b) List any five applications of LEDs	9 5
b) List any five applications of LEDS	5

	Hall	Ticket Number :														
C	code	: 4GC13							<u>.</u>					R-14		
	B.Tech. I Year Supplementary Examinations May 2017															
	Engineering Chemistry (Common to all Branches)															
	Max	. Marks: 70		(Con	nmo	n to	ali f	sranc	cnes)			Tim	ne: 3 Hc	ours	
		nswer all five units	s by cho	posing				fron	n ea	ch ur	nit (t	5 x 14			015	
						***** NIT-										
1	2)	What is meant by	hordna	oo of y				unit	•							7M
1.	a) b)	a) What is meant by hardness of water? Give its unitsb) What is meant by carbonate and non-carbonate hardness of water? Explain with examples.											7M			
	D)	what is meant by o	Carbona	le anu	non-o		R	naru	11622	OI Wa	aler	схріа		nexamp	162.	7 101
2	a)	Write brief accou	nt on Pr	imina :	and f											7M
2	b)	0.5 g of CaCO ₃ w		•			•	dilute	nd to	1000) ml	50 m	loft	his solut	tion	, 101
	0)	required 48 mL o														
		mL of EDTA solu									•		•	•		
		required 10 mL of	f EDTA	solutio			i	ne di	ere	nt kir	nds o	of harc	Iness	in ppm.		7M
_				_		NIT-										
3.		Define galvanic of the different elect		•			-				and	catho	ode is	s +ve. W	rite	14M
				actions		urat	OR	SIECU	oues	.						14101
4.	a)	Discuss the how	the nati	ure of t	he m	etali		nces	: the	rate	ofco	nrosic	'n			7M
т.	b)	Explain the rustin												on		7M
	0)		gerner		r	NIT–		01100			1001)	, 01 00				
5.		Write notes on														
		(a) Tacticity														
		(b) Vulcanization	of rubb	er.												14M
							OR									
6.		What are the poly	/mers?	Explai	n the	e app	licati	ons	of po	lyme	rs in	differ	ent fie	elds.		14M
					U	NIT-	IV									
7.	a)	Explain the different	ence be	tween	gros	s cal	orific	: valu	e an	d net	calc	orific v	alue.			7M
	b)	What is the different	ence be	etween	prox	imat	e ana	alysis	and	ultin	nate	analy	sis of	coal?		7M
							OR									
8.	a)	What are the maj	or cons	tituent	of LF	PG a	nd N	atura	l gas	?						7M
	b)	Why excess air is	s require	ed for c	omp	lete o	comb	oustic	on?							7M
					U	NIT–	V									
9.		Define refractorie						terist	ics	of g	ood	refrac	ctory?	9 Give	the	
		classification of re	etractori	ies with	n exa	mple										14M
40		Define Min in C	11	14 -1 -1	·····		OR					n				
10.		Define Viscosity?	HOW IS	it dete	rmin	ed by **		dwoc	od Vi	scom	leter'	(14M
						ጥጥ	•									

	На	I Ticket Number :															-
ı د	Cod	e: 4GC12								I			l		R- 1	14	
B.Tech. I Year Supplementary Examinations May 2017																	
Engineering Physics																	
(Common to all Branches) Max. Marks: 70 Time: 3 Hours																	
		Answer all five units	s by c	hoc	osing		que *****		fron	n ead	ch ur	nit (5	5x14				
						UN	IIT–I										
1.	a)	Write few application	ons of	f las	ers												4M
	b)	Describe the newto	on's ri	ngs	form	atior			ent.								10M
_							OF	२									
2	a)	Explain the charac					_										4M
	b)	Explain the constru	uction	anc	l wor	•	of op I IT–II		fibre	•							10M
3.	a)	What are Miller indi	ces? E	Expl	ain th	ne pro	ocedu	ure fo	or find	ling N	/liller	indic	es. Gi	ive	one ex	ample	10M
	b)	Draw the planes (2	211), ((100) and	d and	d (22	0)									4M
							(OR									
4.	a)	What are propertie	s of u	Itras	sonic	s?											4M
	b)	Describe any one	methc	od fo	or the				ultras	onics	5.						10M
F	c)	State and evaluin I		nha			IT–II		vinla								сM
5.	a) b)	State and explain I			-				-	ite w		nath					6M 8M
	b)	Define de-Broglie	Juai II	atui	6 01	ener		DR			avele	ingu					OIVI
6	a)	Give the salient fea	atures	s of I	≺roni	ia-Pe			ല								10M
0.	b)	Discuss the origin				-	-										4M
	,						IT–I\										
7.	a)	With symbol expl	lain tl	he	cons	truct	ion a	and	work	ing	of P	hoto	diod	de.	Discu	ss its	
		characteristics.															10M
	b)	Explain the role of	LED a	& Pł	noto	diode		•	al fibr	e cor	nmu	nicat	ion sy	yste	ems.		4M
								OR									
8.	a)	Describe different and its temperature	•••		-		mate	erials	s in te	erms	of th	neir s	spin di	lipo	le aligr	nment	10M
	b)	Define magnetic di magnetic materials	•	nom	nent.	List	out v	ariou	IS SOI	urces	ofm	nagn	etic di	ipol	le mom	nent in	4M
						UN	IT–V	'									
9.	a)	What is Meissner e	effect?	?													4M
	b)	Explain about the f	flux ex	kclus	sion	princ	iple e	exhib	ited	by the	e sup	perco	onduc	tor	S		10M
							(OR									
10.	a)	What are nanomat	erials	? W	hy d	o the	y exl	nibit	differ	ent p	rope	rties	?				8M
	b)	Explain the types of	of nan	oma	ateria	als ba	sed **		imen	siona	alities	6					6M